



## 深圳市南天星电子科技有限公司

Freescale

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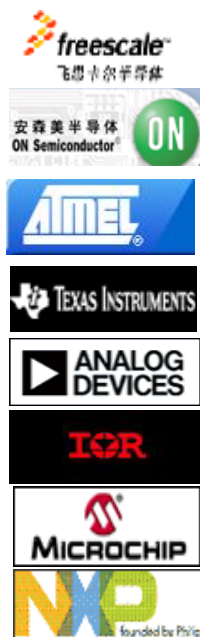
德州仪器

模拟器件

国际整流器

微芯

恩智浦



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# RF Product

## Focus Products

Quarter 4, 2008  
SG1009Q42008 Rev 0

RF Industrial, Scientific and Medical Transistors  
RF LDMOS Power Transistors  
RF GaAS Power Transistors  
RF WiMAX, WiBro, BWA Power Transistors  
RF Amplifier ICs and Modules  
RF General Purpose Amplifiers  
RF Modulators, Booster - Splitter, Stereo Encoders, Silicon Tuners

### RF Industrial, Scientific and Medical Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W	
MRF6VP11KH	U	10-150	1000 Peak	Pulsed	50	26/130	71	0.03
MRF6VP21KH	U	10-235	1000 Peak	Pulsed	50	24/235	67.5	0.03
MRF6VP41KH/HS	U	10-450	1000 Peak	Pulsed	50	20/450	64	0.03
MRF6V2010N/NB	U	10-450	10 CW	1 - Tone	50	23.9/220	62	3.0
MRF6V2150N/NB	U	10-450	150 CW	1 - Tone	50	25/220	68.3	0.24
MRF6V2300N/NB	U	10-600	300 CW	1 - Tone	50	25.5/220	68	0.24
MRF6V4300N/NB★	U	10-600	300 CW	1 - Tone	50	22/450	60	0.24
MRF6VP2600H★	U	10-250	125 W AVG	OFDM	50	25/225	28.5	0.20
MW6IC2420NB	I/O	2450	20 CW	1 - Tone	28	19.5/2450	27	1.8
MRF6S24140H/HS	I/O	2450	140 CW	1 - Tone	28	13.2/2450	45	0.29
MRF6P24190H	I/O	2450	190 CW	1 - Tone	28	13.2/2450	46.2	0.22

### TV Broadcast - LDMOS Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W	
MW6S004N	U	1-2000	4 PEP	2-Tone	28	18/1960	33	8.8
MW6S010N/GN	U	450-1500	10 PEP	2-Tone	28	18/960	32	2.85
MRFE6S9045N	U	880	10 AVG	N-CDMA	28	22.1/880	32	1.0
MRFE6S9060N	U	880	14 AVG	N-CDMA	28	21.1/880	33	0.77
MRF377H	I/O	470-860	45 AVG	OFDM	32	18.2/860	23	0.27
MRFE6P3300H	I/O	470-860	270 PEP	2-Tone	32	20.4/860	44.8	0.23
MRF6VP3450H/HS★	I	470-860	90 AVG	OFDM	50	22.5/860	28	0.27

### Cellular - To 500 MHz - LDMOS Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W	
MW6S004N	U	1-2000	4 PEP	2-Tone	28	18/1960	33	8.8
MW6S010N/GN	U	450-1500	10 PEP	2-Tone	28	18/960	32	2.85
MRF5S4125N/NB	I	450-480	25 AVG	N-CDMA	28	23/465	30	0.33

<sup>(37)</sup>U = Unmatched; I = Input; I/O = Input/Output.

★New Product

### Cellular - To 1000 MHz - LDMOS Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W
MW6S004N	U   1-2000	4 PEP	2-Tone	28	18/1960	33	8.8
MW6S010N/GN	U   450-1500	10 PEP	2-Tone	28	18/960	32	2.85
MRFE6S9045N	U   880	10 AVG	N-CDMA	28	22.1/880	32	1.0
MRFE6S9060N	U   880	14 AVG	N-CDMA	28	21.1/880	32.1	0.77
MW5IC970NB	I   800-900	70 PEP	2-Tone	28	30/870	48	5.2/0.8
MRFE6S9125N/NB	I   880	27 AVG	N-CDMA	28	20.2/880	31	0.44
MRFE6S9130H/HS	I   880	27 AVG	N-CDMA	28	19.2/880	30.5	0.45
MRFE6S9135H/HS	I/O   940	39 AVG	W-CDMA	28	21/940	32.3	0.39
MRFE6S9160H/HS	I   880	35 AVG	N-CDMA	28	21/880	31	0.31
MRFE6S9200H/HS	I   880	58 AVG	W-CDMA	28	21/880	35	0.29
MRF8S9200N <sup>(46e)</sup>	I/O   940	58 AVG	W-CDMA	28	19.5/940	36	—
MRFE6S9201H/HS	I   880	40 AVG	N-CDMA	28	20.8/880	31.3	0.34
MRFE6S9205H/HS	I/O   880	58 AVG	W-CDMA	28	21.2/880	34	0.27
MRFE6P9220H <sup>(46b)</sup>	I/O   880	47 AVG	N-CDMA	28	20/880	30	—

### General Purpose LDMOS Drivers

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W
MW6S004N	U   1-2000	4 PEP	2-Tone	28	18/1960	33	8.8
MW6S010N/GN	U   450-1500	10 PEP	2-Tone	28	18/960	32	2.85
MRF6S20010N/GN	I   1600-2200	10 PEP	2-Tone	28	15.5/2170	36	5.9

### 1500 MHz - LDMOS Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W
MRF7S15100H/HS★	I/O   1470-1510	23 AVG	W-CDMA	28	19.5/1510	32	0.65

### 1800 to 2000 MHz - LDMOS Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W
MRF6S20010N/GN	I   1805-1990	4 AVG	EDGE	28	16/1805,1880	33	2.5
MRF6S18060N/NB	I/O   1800-2000	60 CW	1-Tone	26	15/1990	50	0.81
MRF6S18100N/NB	I/O   1805-1990	100 CW	1-Tone	28	14.5/1930,1990	49	0.51
MRF7S18125AH/AHS <sup>(46b)</sup>	I/O   1805-1880	125 CW	1-Tone	28	17/1880	55	—
MRF7S18125BH/BHS <sup>(46b)</sup>	I/O   1930-1990	125 CW	1-Tone	28	16/1990	55	—
MRF7S18170H/HS	I/O   1805-1880	50 AVG	W-CDMA	28	17.5/1880	31	0.27
MRF6P18190H	I/O   1805-1880	44 AVG	W-CDMA	28	15.9/1805,1880	27.5	0.27

<sup>(37)</sup>U = Unmatched; I = Input; I/O = Input/Output.

<sup>(46)</sup>To be introduced: a) 2Q08; b) 3Q08; c) 4Q08; d) 1Q09; e) 2Q09.

★New Product

**1800 to 2000 MHz - LDMOS Power Transistors (continued)**

Product	Frequency Band <sup>(37)</sup> MHz		P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W
MRF6S20010N/GN	I	1930-1990	1 AVG	N-CDMA	28	15.5/1990	16	2.5
MRF5S19060N/NB	I/O	1930-1990	12 AVG	N-CDMA	28	14/1990	23	0.80
MRF6S19060N/NB	I/O	1930-1990	12 AVG	N-CDMA	28	16/1990	26	0.84
MRF7S19080H/HS	I/O	1930-1990	24 AVG	W-CDMA	28	18/1990	32	0.60
MRF6S19100N/NB	I/O	1930-1990	22 AVG	N-CDMA	28	14.5/1990	25.5	0.61
MRF6S19100H/HS	I/O	1930-1990	22 AVG	N-CDMA	28	16.1/1990	28	0.44
MRF7S19100N/NB	I/O	1930-1990	29 AVG	W-CDMA	28	17.5/1990	30	0.57
MRF6S19120H/HS	I/O	1930-1990	19 AVG	N-CDMA	28	15/1990	21.5	0.43
MRF7S19120N	I/O	1930-1990	36 AVG	W-CDMA	28	18/1990	32	0.43
MRF5S19130HS	I/O	1930-1990	26 AVG	N-CDMA	28	13/1990	25	0.40
MD7P19130H/HS★	I/O	1930-1990	40 AVG	W-CDMA	28	20/1990	30	0.31
MRF6S19140H/HS	I/O	1930-1990	29 AVG	N-CDMA	28	16/1990	27.5	0.33
MRF5S19150H	I/O	1930-1990	32 AVG	N-CDMA	28	14/1990	26	0.41
MRF7S19170H/HS	I/O	1930-1990	50 AVG	W-CDMA	28	17.2/1990	32	0.25
MRF6S19200H/HS	I/O	1930-1990	56 AVG	W-CDMA	28	17.9/1990	29.5	0.35
MRF7S19210H <sup>(46c)</sup>	I/O	1930-1990	63 AVG	W-CDMA	28	19	29	—
MRF7S19210HS <sup>(46c)</sup>	I/O	1930-1990	63 AVG	W-CDMA	28	20	31	—

**2000 to 2200 MHz - LDMOS Power Transistors**

Product	Frequency Band <sup>(37)</sup> MHz		P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W
MRF6S20010N/GN	I	2110-2170	1 AVG	W-CDMA	28	15.5/2170	15	2.5
MRF5P21045N	I/O	2110-2170	10 AVG	W-CDMA	28	14.5/2170	25.5	1.35
MRF5S21045N/NB	I/O	2110-2170	10 AVG	W-CDMA	28	14.5/2170	25.5	1.35
MRF6S21050L/LS	I/O	2110-2170	11.5 AVG	W-CDMA	28	16/2170	27.7	1.16
MRF6S21060N/NB	I/O	2110-2170	14 AVG	W-CDMA	28	15.5/2170	26	0.89
MRF7S21080H/HS	I/O	2110-2170	22 AVG	W-CDMA	28	18/2170	32	0.60
MRF6S21100H/HS	I/O	2110-2170	23 AVG	W-CDMA	28	15.9/2170	27.6	0.45
MRF6S21100N/NB	I/O	2110-2170	23 AVG	W-CDMA	28	14.5/2170	25.5	0.57
MD7IC21100N/GN/NB <sup>(46c)</sup>	I/O	2110-2170	32 AVG	W-CDMA	28	28.5/2170	30	—
MRF7S21110H/HS	I/O	2110-2170	33 AVG	W-CDMA	28	17.3/2170	32.5	0.37
MRF6S21140H/HS	I/O	2110-2170	30 AVG	W-CDMA	28	15.5/2170	27.5	0.35
MRF7S21150H/HS	I/O	2110-2170	44 AVG	W-CDMA	28	17.5/2170	31	0.33
MRF7S21170H/HS	I/O	2110-2170	50 AVG	W-CDMA	28	16/2170	31	0.31
MRF5P21180H	I/O	2110-2170	38 AVG	W-CDMA	28	14/2170	25.5	0.31
MRF6P21190H	I/O	2110-2170	44 AVG	W-CDMA	28	15.5/2170	26.5	0.25
MRF6S21190H/HS	I/O	2110-2170	54 AVG	W-CDMA	28	16/2170	29	0.29

<sup>(37)</sup>U = Unmatched; I = Input; I/O = Input/Output.

<sup>(46)</sup>To be introduced: a) 2Q08; b) 3Q08; c) 4Q08; d) 1Q09; e) 2Q09.

★New Product

### RF GaAs Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	Eff. (Typ)/Freq. %/MHz	θ <sub>JC</sub> °C/W	
MRF7S21210HS★/H <sup>(46c)</sup>	I/O	2110-2170	63 AVG	W-CDMA	28	18.5/2170	29	0.33
MRFG35002N6A	U	DC-6000	0.16 AVG	W-CDMA	6	10/3550	26.5/3550	13.7
MRFG35003AN	U	DC-6000	0.3 AVG	W-CDMA	12	10.8/3550	24.5/3550	15.9
MRFG35003N6A	U	DC-6000	0.45 AVG	W-CDMA	6	10/3550	27/3550	5.9
MRFG35005AN	U	DC-6000	0.45 AVG	W-CDMA	12	11/3550	26/3550	13.7
MRFG35010AN	U	DC-6000	1 AVG	W-CDMA	12	10/3550	25/3550	6.5
MRFG35010A	U	DC-6000	1 AVG	W-CDMA	12	10/3550	25/3550	4.0 <sup>(16)</sup>
MRFG35020A	I	2300-3800	2 AVG	W-CDMA	12	11.5/3500	22/3500	2.7

### RF WiMAX, WiBro, BWA Power Transistors

Product	Frequency Band <sup>(37)</sup> MHz	P <sub>out</sub> (Typ) Watts	Test Signal	V <sub>DD</sub> Volts	Gain (Typ)/Freq. dB/MHz	η Eff. (Typ) %	θ <sub>JC</sub> °C/W	
MRF7S16150H/HS	I/O	1600-1660	32 AVG	WiMAX	28	19.7/1660	25.4	0.34
MRF6S23100H/HS	I/O	2300-2400	20 AVG	W-CDMA	28	15.4/2300, 2400	23.5	0.53
MRF6S23140H/HS	I/O	2300-2400	28 AVG	W-CDMA	28	15.2/2300, 2400	25	0.29
MRF6P23190H	I/O	2300-2400	40 AVG	W-CDMA	28	14/2300, 2400	23.5	0.22
MRF6S27015N/GN	I	2300-2700	3 AVG	W-CDMA	28	14/2600	22	2.0
MW7IC2725N/GN/NB★	I/O	2700	4 AVG	WiMAX	28	28.5/2700	17	1.4
MRF6S27050H/HS	I/O	2500-2700	7 AVG	W-CDMA	28	16/2500, 2700	22.5	0.85
MW7IC2750N/GN/NB★	I/O	2700	8 AVG	WiMAX	28	26/2700	17	0.7
MD7IC2755N/GN/NB <sup>(46c)</sup>	I/O	2700	10 AVG	WiMAX	28	25/2700	25	—
MRF6S27085H/HS	I/O	2600-2700	20 AVG	N-CDMA	28	15.5/2655	23.5	0.50
MRF7S27130H/HS	I/O	2500-2700	23 AVG	WiMAX	28	16.5/2500, 2700	20	0.32
MRF6P27160H	I/O	2600-2700	35 AVG	N-CDMA	28	14.6/2655	22.6	0.29
MRF7S38010H/HS	I/O	3400-3800	2 AVG	WiMAX	30	15/3400, 3600	17	2.05
MW7IC3825N/GN/NB <sup>(46a)</sup>	I/O	3400-3800	5 AVG	WiMAX	28	23.5/3400, 3600	15	—
MRF7S38040H/HS	I/O	3400-3800	8 AVG	WiMAX	30	14/3400, 3600	15.6	0.78
MRF7S38075H/HS	I/O	3400-3800	12 AVG	WiMAX	30	14/3400, 3600	14	0.46
MRFG35002N6A	U	DC-6000	0.16 AVG	W-CDMA	6	10/3550	26.5	13.7
MRFG35003AN	U	DC-6000	0.3 AVG	W-CDMA	12	10.8/3550	24.5	15.9
MRFG35003N6A	U	DC-6000	0.45 AVG	W-CDMA	6	10/3550	27	5.9
MRFG35005AN	U	DC-6000	0.45 AVG	W-CDMA	12	11/3550	26	13.7
MRFG35010AN	U	DC-6000	1 AVG	W-CDMA	12	10/3550	25	6.5
MRFG35010A	U	DC-6000	1 AVG	W-CDMA	12	10/3550	25	4.0 <sup>(16)</sup>
MRFG35020A	I	2300-3800	2 AVG	W-CDMA	12	11.5/3500	22	2.7

<sup>(16)</sup>Class A = 4.1

<sup>(37)</sup>U = Unmatched; I = Input; I/O = Input/Output.

<sup>(46)</sup>To be introduced: a) 2Q08; b) 3Q08; c) 4Q08; d) 1Q09; e) 2Q09.

★New Product

## RF Amplifier ICs and Modules

Product	Frequency Band MHz	P1dB Watts	Gain (Typ) dB	Supply Voltage Volts	System Application
MW7IC915N <sup>(46d)</sup>	728-960	15	37.3	28	W-CDMA
MHVIC915N	746-960	15	30	26	N-CDMA, GSM/GSM EDGE
MWIC930N/GN	746-960	30	30	27	N-CDMA, GSM/GSM EDGE
MW4IC915NB/GNB	860-960	15	30	26	N-CDMA, GSM/GSM EDGE
MWE6IC9100N/GN/NB	869-960	112	33.5	26	GSM/GSM EDGE
MHVIC910HN	921-960	10	39	26	GSM900
MHV5IC1810N	1805-1990	10	29	28	GSM/GSM EDGE
MW6IC2015NB/GNB	1805-1990	15	26	26	GSM/GSM EDGE N-CDMA, W-CDMA
MW4IC2020NB/GNB	1805-1990	20	29	26	N-CDMA, GSM/GSM EDGE
MW7IC2040N/GN/NB <sup>(46c)</sup>	1805-1880 1930-1990	45 30	33 32	28 28	GSM/GSM EDGE W-CDMA
MW7IC18100N/GN/NB	1805-2050	100	30	28	GSM/GSM EDGE
MHV5IC2215N	1930-1990 2130-2170	15 15	27.5 24	28 28	N-CDMA W-CDMA
MW5IC2030NB/GNB	1930-1990	30	23	27	GSM/GSM EDGE, W-CDMA, PHS
MW6IC1940NB/GNB	1920-2000	40	27	28.5	W-CDMA
MHVIC2114N	2110-2170	15	32	27	W-CDMA
MW7IC2220N/GN/NB★	2110-2170	20	31	28	W-CDMA
MW4IC2230NB/GNB	2110-2170	30	31.5	28	W-CDMA
MW6IC2240NB/GNB	2110-2170	40	28	28	W-CDMA
MW7IC2240N/GN/NB	2110-2170	40	30.9	28	W-CDMA
MW7IC2725N/GN/NB★	2700	25	28.5	28	WiMAX
MW7IC2750N/GN/NB★	2700	50	26	28	WiMAX
MD7IC2755N/GN/NB <sup>(46c)</sup>	2700	55	25	28	WiMAX
MW7IC3825N/GN/NB <sup>(46a)</sup>	3400-3800	25	23.5	28	WiMAX

## RF General Purpose Amplifiers

Product	Frequency Band MHz	Supply Voltage (Typ) Volts	Supply Current (Typ) mA	Small Signal Gain (Typ) @ 900 MHz dB	P <sub>1dB</sub> (Typ) @ 900 MHz dBm	3rd Order Intercept (Typ) @ 900 MHz dBm	NF (Typ) @ 900 MHz dB	θ <sub>JC</sub> °C/W
MMG3008N	0-6000	5	38	18.5	15	26	4	84
MMG3011N	0-6000	5	41	15	15	28	4.6	83
MMG3007N	0-6000	5	47	19	16	30	3.8	77
MMG3009N	0-6000	5	70	15	18	34	4.2	81
MMG3012N	0-6000	5	70	19	18.5	34	3.8	85
MMG3H21N★	0-6000	5	90	19.3	20.5	37	5.5	38.6
MMG3015N	0-6000	5	95	15.5	20.5	36	5.6	41.5
MMG3014N★	40-4000	5	135	19.5	25	40.5	5.7	27.4
MMH3111N	250-4000	5	150	12	22.5	44	3.2	37.5
MMG3004N	400-2200	5	250	16*	27*	44*	3.4*	33
MMG3005N	800-2200	5	480	15*	30*	47*	5*	21.5
MMG3006N	400-2400	5	850	17.5	33	49	6.6	7.8

<sup>(46)</sup>To be introduced: a) 2Q08; b) 3Q08; c) 4Q08; d) 1Q09; e) 2Q09.

★New Product

\*@ 2140 MHz

\*@ 2140 MHz

\*@ 2140 MHz

\*@ 2140 MHz

For additional information on RF High Power Products, Tape and Reel Specifications, Case Dimensions for all packages, and a device index, refer to SG46, *RF Product Selector Guide*.

## RF Modulators, Booster - Splitter, Stereo Encoders

Product	Description	Standards	Output Channels	Output Levels	Region/Country	Packaging	Additional Information
MC44CC373CAEF	Multi-standard Modulator	B/G, I, D/K, H, M/N, L	VHF and UHF all channels	82 dB $\mu$ V	All	SOIC-16 (SO-NB)	Notes 1, 2, 5
MC44CC374CAEF	Multi-standard Modulator	B/G, I, D/K, H, M/N	VHF and UHF all channels	82 dB $\mu$ V	All but France	SOIC-16 (SO-NB)	Notes 3, 5
MC44CC374T1AEF	Multi-standard Modulator (higher output)	B/G, I, D/K, H, M/N	VHF and UHF all channels	82 dB $\mu$ V	All but France	SOIC-16 (SO-NB)	Notes 1, 3, 5
MC44CC375AVEF	VHF Modulator (higher output)	B/G, H, M/N	VHF Ch 3 and 4	86 dB $\mu$ V	The Americas	SOIC-16 (SO-NB)	Note 3
MC44C402A	MTS Stereo Encoder	BTSC	N/A	N/A	The Americas	32-pin LQFP	Notes 2, 3
MC44C404EP	NICAM Stereo Encoder	NICAM	B, G, H, I, K1, L	N/A	Europe	32-pin TQFN	Notes 3, 4

### Notes:

- Suffix for RoHS compliant: EF
- Suffix for 32-pin RoHS compliant LQFP: AC

- Suffix for tape & reel: R2
- Suffix for 32-pin RoHS compliant TQFN: EP

- MC44BS373xx and MC44BS374xx will be replaced by MC44CC373/4xx. Contact your local sales office for more information.

## Silicon Tuners (Dual Conversion Receivers)

Product	Supply Voltage	Power Consumption Typ	Noise Figure Typ	Applications
MC44S803EP	3.3	700-997 mW	7.0 dB	High performance analog and digital TV, computer TV cards, cable data modems, digital terrestrial TV, DVD-R and DVR/PVR

## RF Design Tools

### RF HIGH POWER MODELS

Freescale Semiconductor continues to populate its RF High Power Model Library with MET and Root models. All product models available in the RF High Power Model Library (Root and MET) include package, bond wire and internal matching network effects.

The MET model for RF High Power transistors and RF ICs is a nonlinear model that examines both electrical and thermal phenomena and can account for dynamic self-heating effects of device performance. It is specifically tailored to model high power RF transistors and RF ICs used in wireless base station applications.

The MET model is capable of performing small-signal, large-signal, harmonic-balance, noise and transient simulations.

The current release of the MET model is available for these tools:

- Agilent EEsof ADS® (UNIX, PC and Red Hat® Linux®) nonlinear circuit simulator
- Applied Wave Research Microwave™ Office

For more information and latest releases supported, go to <http://www.freescale.com/rf/models>.

### RF POWER ELECTROMIGRATION MTTF CALCULATION PROGRAM

#### PROGRAM FUNCTIONALITY

This MTTF/FIT calculator software is designed to assist our customers in estimating the LDMOS device reliability in terms of electromigration wear-out failures. The program evaluates LDMOS device Median-Time-To-Failure (MTTF) using Black's Equations.

#### MTTF CALCULATOR AVAILABILITY

RF Power MTTF calculators are being added to the Freescale Semiconductor web site for all RF LDMOS Power discrete transistor and IC devices. Go to <http://www.freescale.com/rf> and select Software & Tools/Development Tools/Calculators.

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